

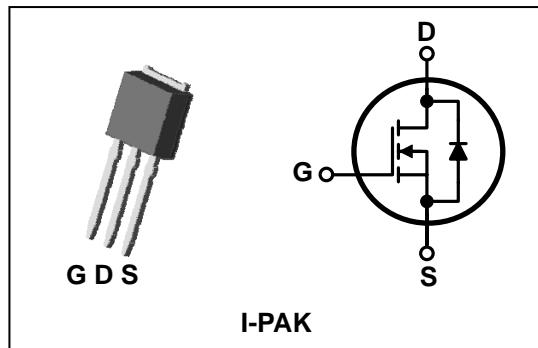
## SWITCHING REGULATOR APPLICATIONS

**Features**

- High Voltage:  $BV_{DSS}=600V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=3.4\text{pF}$ (Typ.)
- Low gate charge :  $Q_g=7.0\text{nC}$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=4.7\Omega$ (Max.)

**Ordering Information**

Type No.	Marking	Package Code
SMK0260I	SMK0260	I-PAK

**PIN Connection**

**Absolute maximum ratings ( $T_c=25^\circ\text{C}$  unless otherwise noted)**

Characteristic	Symbol		Rating	Unit
Drain-source voltage	$V_{DSS}$		600	V
Gate-source voltage	$V_{GSS}$		$\pm 30$	V
Drain current (DC) *	$I_D$	$T_c=25^\circ\text{C}$	2.0	A
		$T_c=100^\circ\text{C}$	1.35	A
Drain current (Pulsed) *	$I_{DM}$		8.0	A
Drain power dissipation	$P_D$		48	W
Avalanche current (Single) ②	$I_{AS}$		2.0	A
Single pulsed avalanche energy ②	$E_{AS}$		130	mJ
Avalanche current (Repetitive) ①	$I_{AR}$		2.0	A
Repetitive avalanche energy ①	$E_{AR}$		5.6	mJ
Junction temperature	$T_J$		150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$		-55~150	$^\circ\text{C}$

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max	Unit
Thermal resistance	$R_{th(J-C)}$	-	2.6	$^\circ\text{C}/\text{W}$
	$R_{th(J-A)}$	-	62.5	

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$I_D=250 \mu\text{A}, V_{GS}=0\text{V}$	600	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=250 \mu\text{A}, V_{GS}=V_{DS}$	2.0	-	4.0	V
Drain-source cut-off current	$I_{DSS}$	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
		$V_{DS}=600\text{V}, V_{GS}=0\text{V}, T_C=125^\circ\text{C}$			200	
Gate leakage current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance <sup>(4)</sup>	$R_{DS(\text{on})}$	$V_{GS}=10\text{V}, I_D=1.0\text{A}$	-	3.9	4.7	$\Omega$
Forward transfer conductance <sup>(4)</sup>	$g_{fs}$	$V_{DS}=10\text{V}, I_D=1.0\text{A}$	-	5	-	S
Input capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=25\text{V}$ $f=1 \text{ MHz}$	-	250	334	pF
Output capacitance	$C_{oss}$		-	20	27	
Reverse transfer capacitance	$C_{rss}$		-	3.4	4.6	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=300\text{V}, I_D=2.0\text{A}$ $R_G=25\Omega$	-	9	-	ns
Rise time	$t_r$		-	25	-	
Turn-off delay time	$t_{d(off)}$		-	24	-	
Fall time	$t_f$		-	28	-	
Total gate charge	$Q_g$	$V_{DS}=480\text{V}, V_{GS}=10\text{V}$ $I_D=2.0\text{A}$	-	7.0	9.5	nC
Gate-source charge	$Q_{gs}$		-	1.5	-	
Gate-drain charge	$Q_{gd}$		-	4.7	-	

**Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Source current (DC)	$I_S$	Integral reverse diode in the MOSFET	-	-	2.0	A
Source current (Pulsed) <sup>(1)</sup>	$I_{SP}$		-	-	8.0	
Forward voltage <sup>(4)</sup>	$V_{SD}$	$V_{GS}=0\text{V}, I_S=2.0\text{A}$	-	-	1.4	V
Reverse recovery time	$t_{rr}$	$I_S=2.0\text{A}, V_{GS}=0\text{V}$ $dI_S/dt=100\text{A}/\mu\text{s}$	-	230	-	ns
Reverse recovery charge	$Q_{rr}$		-	1.0	-	$\mu\text{C}$

Note :

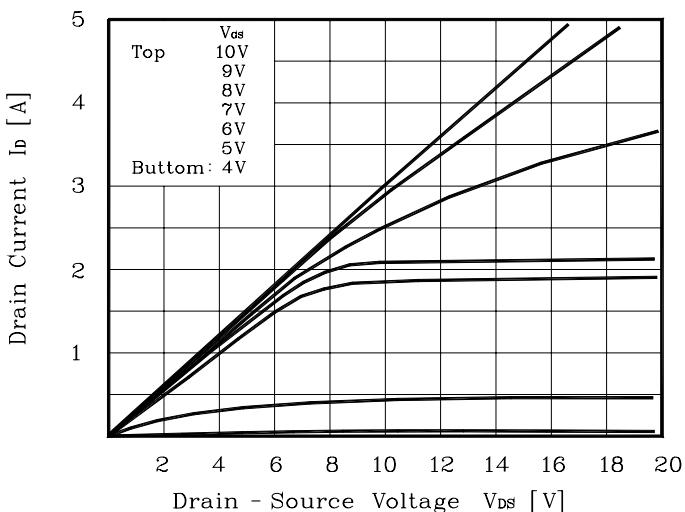
① Repetitive rating : Pulse width limited by maximum junction temperature

②  $L=59.5\text{mH}, I_{AS}=2.0\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$ , Starting  $T_J = 25^\circ\text{C}$ ③ Pulse Test : Pulse width  $\leq 300 \mu\text{s}$ , Duty cycle  $\leq 2\%$ 

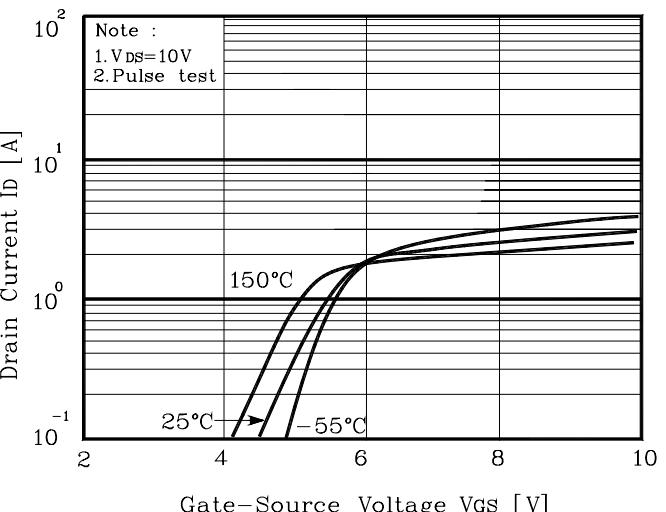
④ Essentially independent of operating temperature

## Electrical Characteristic Curves

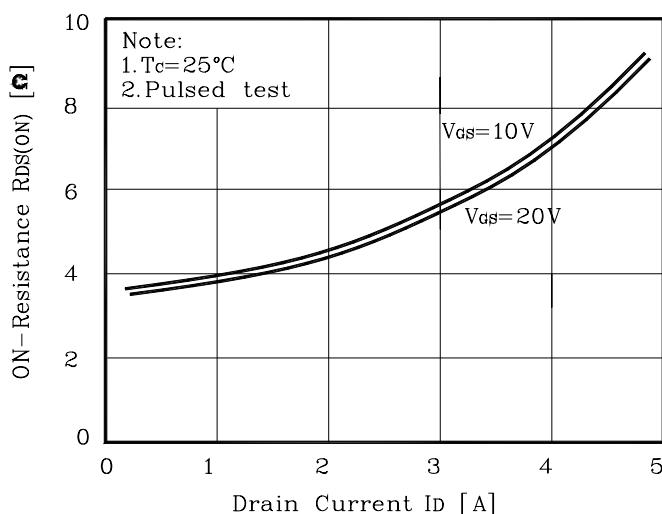
**Fig. 1  $I_D$  -  $V_{DS}$**



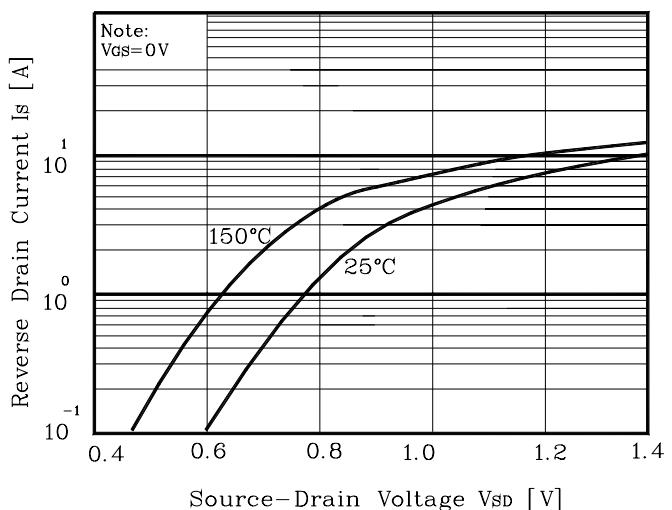
**Fig. 2  $I_D$  -  $V_{GS}$**



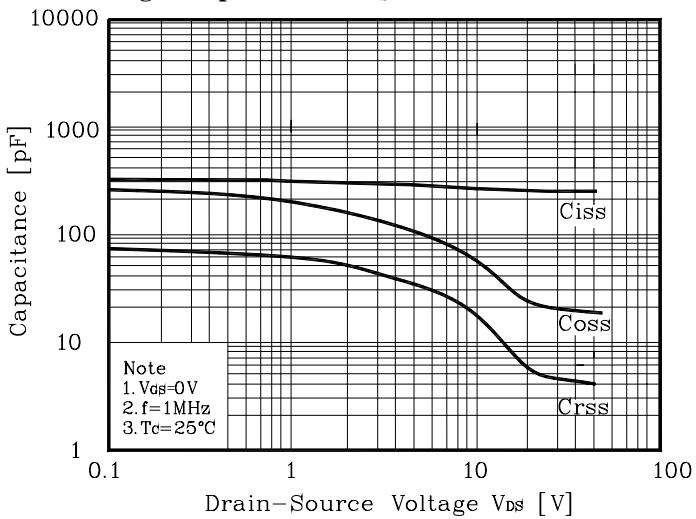
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



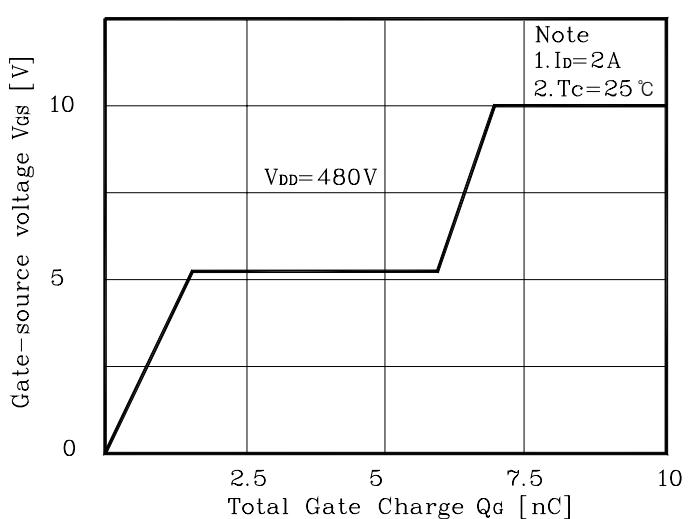
**Fig. 4  $I_S$  -  $V_{SD}$**



**Fig. 5 Capacitance -  $V_{DS}$**

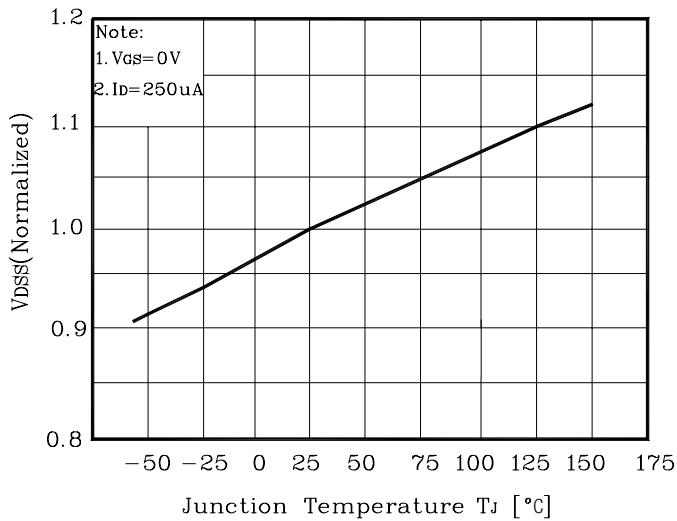


**Fig. 6  $V_{GS}$  -  $Q_G$**

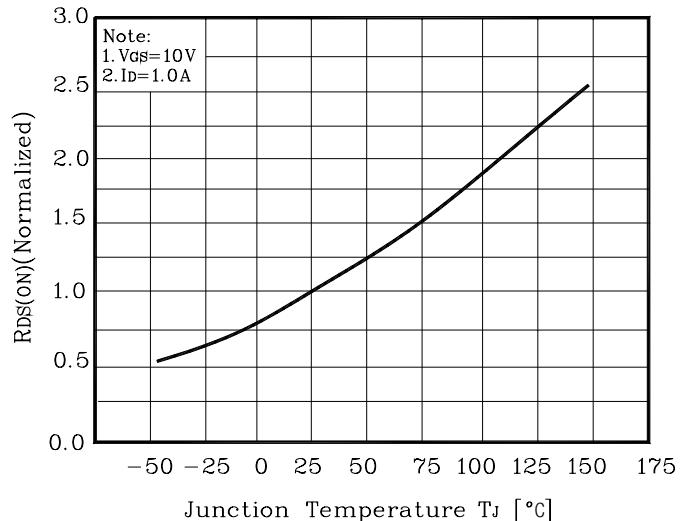


## Electrical Characteristic Curves

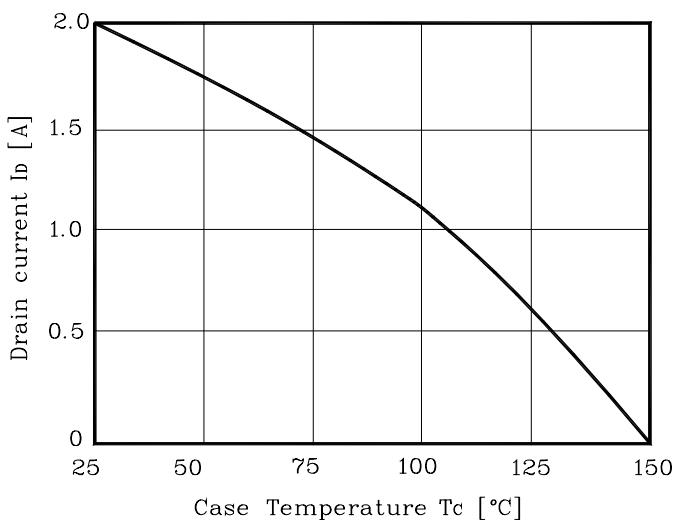
**Fig. 7  $V_{DSS}$  -  $T_J$**



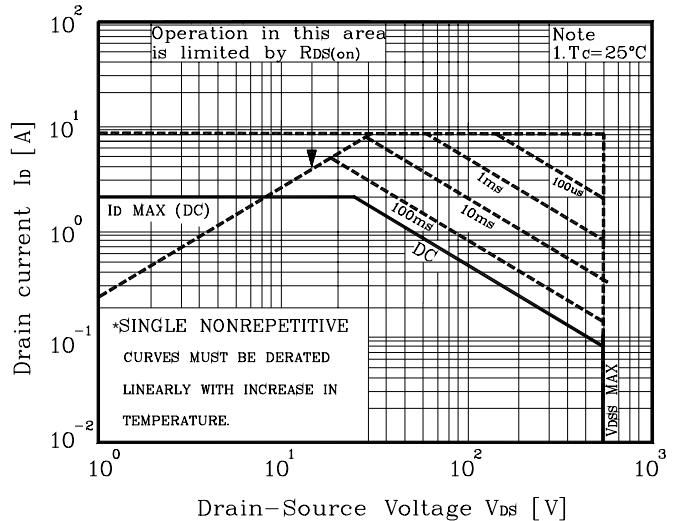
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



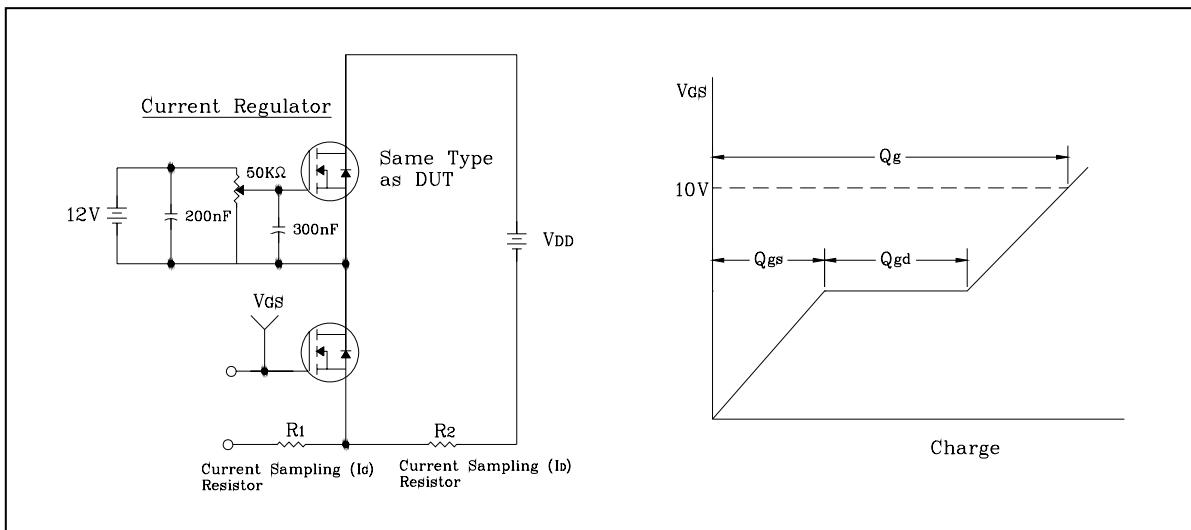
**Fig. 9  $I_D$  -  $T_c$**



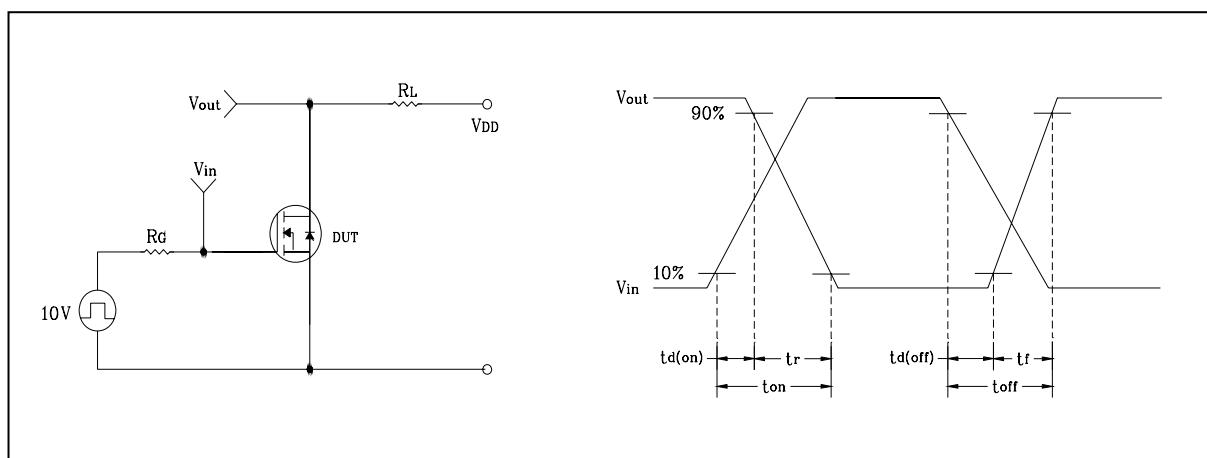
**Fig. 10 Safe Operating Area**



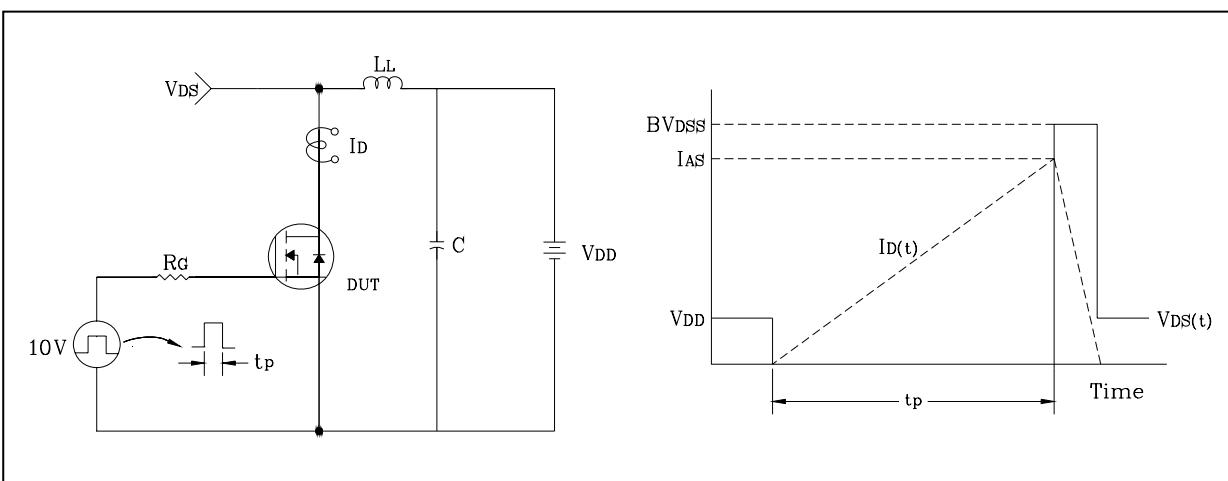
**Fig. 11 Gate Charge Test Circuit & Waveform**



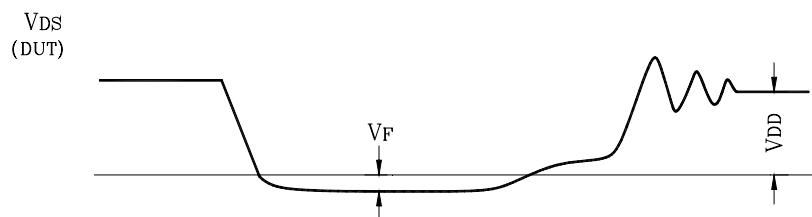
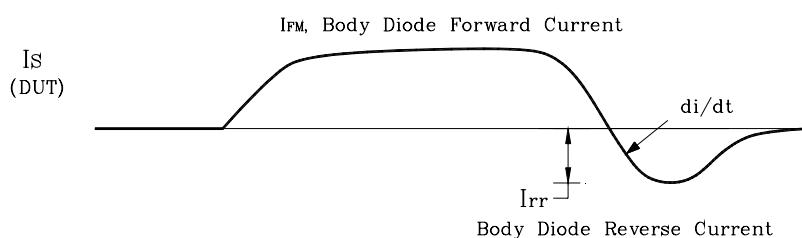
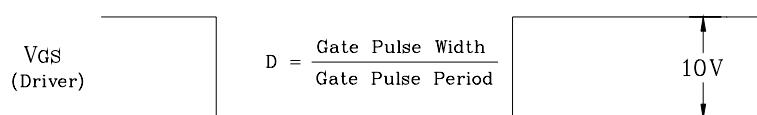
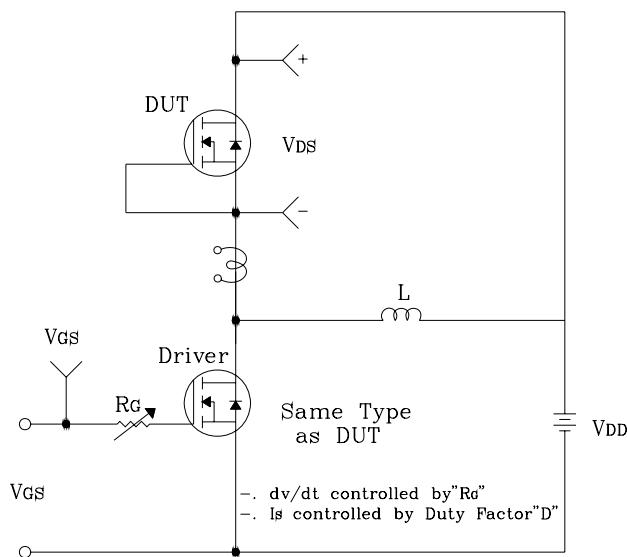
**Fig. 12 Resistive Switching Test Circuit & Waveform**

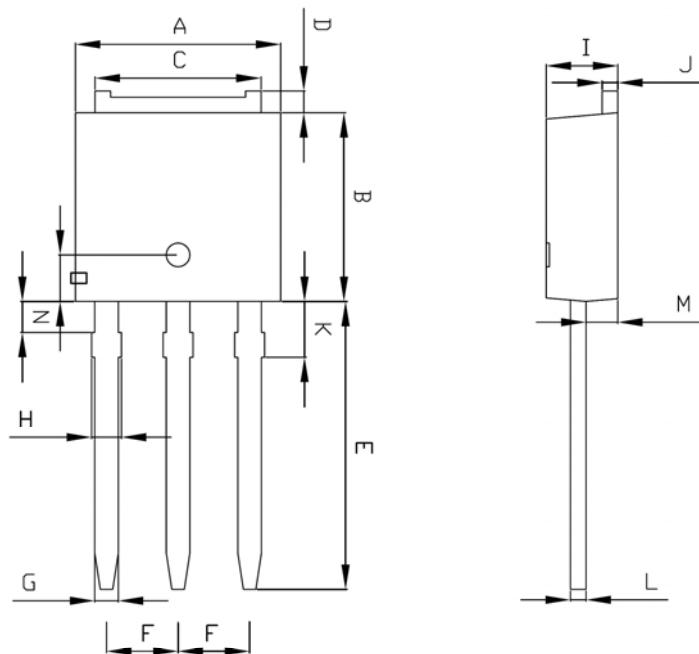


**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**



**Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform**



**Outline Dimension**

SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	6.40	6.60	6.80	
B	5.90	6.10	6.30	
C	5.04	5.34	5.64	
D	0.50	0.70	0.90	
E	9.00	9.30	9.60	
F	2.10	2.30	2.50	
G	0.66	0.76	0.86	
H	0.96 MAX			
I	2.20	2.30	2.40	
J	0.40	0.50	0.60	
K	1.60	1.80	2.00	
L	0.40	0.50	0.60	
M	0.72	1.02	1.32	
N	0.90	1.00	1.10	
O	1.50			

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